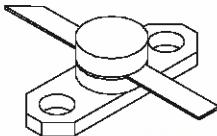



MSC1004M
**RF & MICROWAVE TRANSISTORS
AVIONICS APPLICATIONS**

- 1025 - 1150 MHz
- RUGGEDIZED VSWR $\infty:1$
- INTERNAL INPUT MATCHING
- LOW THERMAL RESISTANCE
- $P_{out} = 4.0$ W MIN. WITH 9.0 dB GAIN


.b280 2LFL (SO68)
epoxy sealed

ORDER CODE
MSC1004M

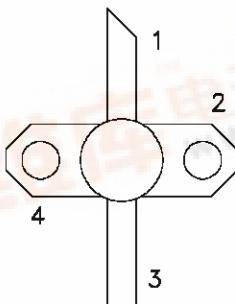
BRANDING
1004M

DESCRIPTION

The MSC1004M is a low-level Class C pulsed transistor specifically designed for DME/IFF driver or output applications.

These devices are capable of withstanding a $\infty:1$ load VSWR at any phase angle under full rated conditions. Low RF thermal resistance and automatic bonding techniques ensure high reliability and product consistency.

The MSC1004M is housed in the IMPAC™ package with internal input matching.

PIN CONNECTION

1. Collector 3. Emitter
2. Base 4. Base

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^\circ\text{C}$)

Symbol	Parameter	Value	Unit
P_{DISS}	Power Dissipation* ($T_c \leq 100^\circ\text{C}$)	18	W
I_c	Device Current*	650	mA
V_{cc}	Collector-Supply Voltage*	32	V
T_J	Junction Temperature	200	$^\circ\text{C}$
T_{STG}	Storage Temperature	– 65 to +150	$^\circ\text{C}$

THERMAL DATA


$R_{TH(j-c)}$	Junction-Case Thermal Resistance*	5	$^\circ\text{C/W}$
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*Applies only to rated RF amplifier operation

ELECTRICAL SPECIFICATIONS ($T_{case} = 25^\circ\text{C}$)

STATIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BV_{CBO}	$I_C = 1 \text{ mA}$ $I_E = 0 \text{ mA}$	45	—	—	V
BV_{CER}	$I_C = 5 \text{ mA}$ $R_{BE} = 10 \Omega$	45	—	—	V
BV_{EBO}	$I_E = 1 \text{ mA}$ $I_C = 0 \text{ mA}$	3.5	—	—	V
I_{CES}	$V_{CE} = 28 \text{ V}$	—	—	1.0	mA
h_{FE}	$V_{CE} = 5 \text{ V}$ $I_C = 200 \text{ mA}$	30	—	300	—

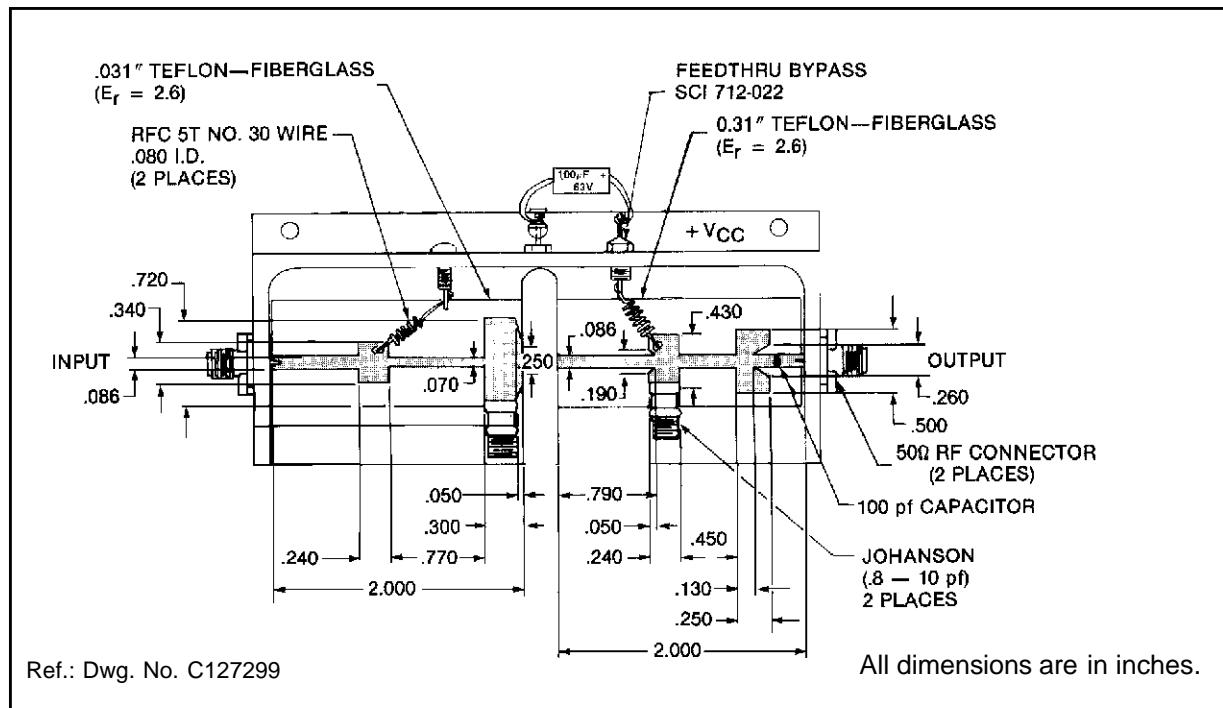
DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
P_{OUT}	$f = 1025 - 1150 \text{ MHz}$ $P_{\text{IN}} = 500 \text{ mW}$ $V_{CC} = 28 \text{ V}$	4.0	—	—	W
η_{C}	$f = 1025 - 1150 \text{ MHz}$ $P_{\text{IN}} = 500 \text{ mW}$ $V_{CC} = 28 \text{ V}$	35	—	—	%
G_{P}	$f = 1025 - 1150 \text{ MHz}$ $P_{\text{IN}} = 500 \text{ mW}$ $V_{CC} = 28 \text{ V}$	9.0	—	—	dB

Note: Pulse Width = $10\mu\text{Sec}$

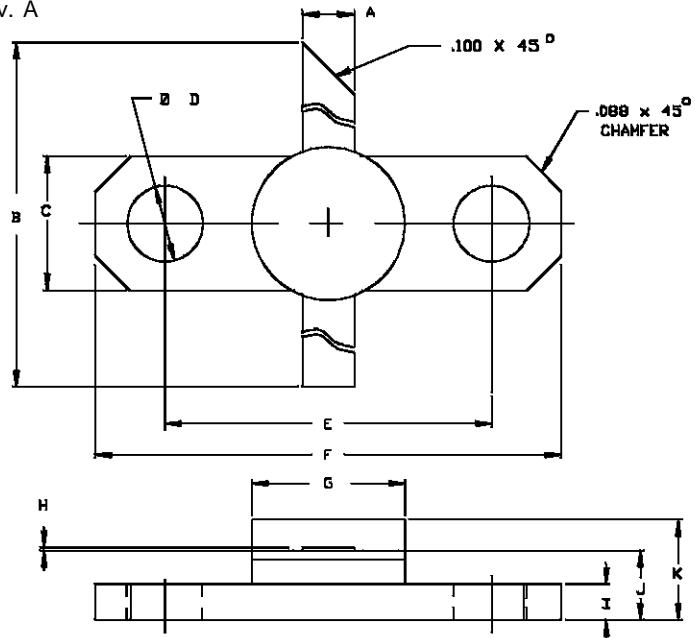
Duty Cycle = 1%

TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No. 12-0218 rev. A



SGS-THOMSON MICROELECTRONICS		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.095/2.41	.105/2.67
B	.1050/26.67	
C	.245/6.22	.255/6.48
D	.120/3.05	.140/3.56
E	.552/14.02	.572/14.53
F	.790/20.07	.810/20.57
G		.205/7.24
H	.003/0.08	.007/0.18

CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
I	.052/1.32	.072/1.83
J	.120/3.05	.130/3.30
K		.210/5.33

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